

Elektrische Eigenschaften

Electrical properties

Höchstzulässige Werte

Maximum rated values

Periodische Vorwärts- und Rückwärts-Spitzensperrspannung	repetitive peak forward off-state and reverse voltages	$t_{vj} = -40^{\circ}\text{C} \dots t_{vj\text{max}}$	$V_{\text{DRM}}, V_{\text{RRM}}$	200,400 V 600,800 V
Vorwärts-Stoßspitzensperrspannung	non repetitive peak forward off-state voltage	$t_{vj} = -40^{\circ}\text{C} \dots t_{vj\text{max}}$	$V_{\text{DSM}} = V_{\text{DRM}}$	
Rückwärts-Stoßspitzensperrspannung	non repetitive peak reverse voltage	$t_{vj} = +25^{\circ}\text{C} \dots t_{vj\text{max}}$	$V_{\text{RSM}} = V_{\text{RRM}}$	+ 50 V
Durchlaßstrom-Grenzeffektivwert	RMS on-state current	$t_c = 85^{\circ}\text{C}$	I_{TRMSM}	220 A
Dauerrenzstrom	average on-state current	$t_c = 64^{\circ}\text{C}$	I_{TAVM}	102 A 140 A
Stoßstrom-Grenzwert	surge current	$t_{vj} = 25^{\circ}\text{C}, t_p = 10 \text{ ms}$ $t_{vj} = t_{vj\text{max}}, t_p = 10 \text{ ms}$	I_{TSM}	3200 A 2750 A
Grenzlastintegral	Pt-value	$t_{vj} = 25^{\circ}\text{C}, t_p = 10 \text{ ms}$ $t_{vj} = t_{vj\text{max}}, t_p = 10 \text{ ms}$	I^2t	51000 A ² s 37800 A ² s
Kritische Stromsteilheit	critical rate of rise of on-state current	$v_D \leq 67\% V_{\text{DRM}}, f = 50 \text{ Hz}$ $i_{\text{GM}} = 0,6 \text{ A}, di_G/dt = 0,6 \text{ A}/\mu\text{s}$	$(di/dt)_{\text{cr}}$	200 A/ μs
Kritische Spannungssteilheit	critical rate of rise of off-state voltage	$t_{vj} = t_{vj\text{max}}, v_D = 67\% V_{\text{DRM}}$	$(dv/dt)_{\text{cr}}$	B: 50 50 V/ μs c*: 500 500 V/ μs L: 500 50 V/ μs M*: 1000 500 V/ μs

Charakteristische Werte

Characteristic values

Durchlaßspannung	on-state voltage	$t_{vj} = t_{vj\text{max}}, I_T = 500 \text{ A}$	V_T	max. 1,95 V
Schleusenspannung	threshold voltage	$t_{vj} = t_{vj\text{max}}$	$V_{T(\text{TO})}$	1,2 V
Ersatzwiderstand	slope resistance	$t_{vj} = t_{vj\text{max}}$	r_T	1,4 m Ω
Zündstrom	gate trigger current	$t_{vj} = 25^{\circ}\text{C}, v_D = 6 \text{ V}$	I_{GT}	max. 150 mA
Zündspannung	gate trigger voltage	$t_{vj} = 25^{\circ}\text{C}, v_D = 6 \text{ V}$	V_{GT}	max. 2 V
Nicht zündender Steuerstrom	gate non-trigger current	$t_{vj} = t_{vj\text{max}}, v_D = 6 \text{ V}$	I_{GD}	max. 10 mA
Nicht zündende Steuerspannung		$t_{vj} = t_{vj\text{max}}, v_D = 0,5 V_{\text{DRM}}$	V_{GD}	max. 0,25 V
Haltestrom	holding current	$t_{vj} = 25^{\circ}\text{C}, v_D = 6 \text{ V}, R_A = 5 \Omega$	I_H	max. 250 mA
	latching current	$t_{vj} = 25^{\circ}\text{C}, v_D = 6 \text{ V}, R_{\text{GK}} \geq 10 \Omega$ $i_{\text{GM}} = 0,6 \text{ A}, di_G/dt = 0,6 \text{ A}/\mu\text{s}, t_g = 20 \mu\text{s}$	I_L	max. 750 mA
Vorwärts- u. Rückwärts-Sperrstrom	forward off-state and reverse Currents	$t_{vj} = t_{vj\text{max}}, v_D = V_{\text{DRM}}, v_R = V_{\text{RRM}}$	i_D, i_R	max. 30 mA
Zündverzug	gate controlled delay time	$t_{vj} = 25^{\circ}\text{C}, i_{\text{GM}} = 0,6 \text{ A}, di_G/dt = 0,6 \text{ A}/\mu\text{s}$ siehe Techn. Erl./see Techn. Inf.	t_{gd}	max. 1,4 μs
Freiwerdezeit			t_q	B*: max. 10 μs D: max. 15 μs

Thermische Eigenschaften

Thermal properties

Innerer Wärmewiderstand	thermal resistance, junction to case	$\theta = 180^{\circ} \text{ el, sin DC}$	R_{thJC}	max. 2,26 $^{\circ}\text{C}/\text{W}$ max. 0,24 $^{\circ}\text{C}/\text{W}$
Höchstzul. Sperrschichttemperatur	max. junction temperature		$t_{vj\text{max}}$	125 $^{\circ}\text{C}$
Betriebstemperatur	Operating temperature		$t_{c\text{op}}$	-40 ... + 125 $^{\circ}\text{C}$
Lagertemperatur	storage temperature		t_{stg}	-40 ... + 150 $^{\circ}\text{C}$

Mechanische Eigenschaften

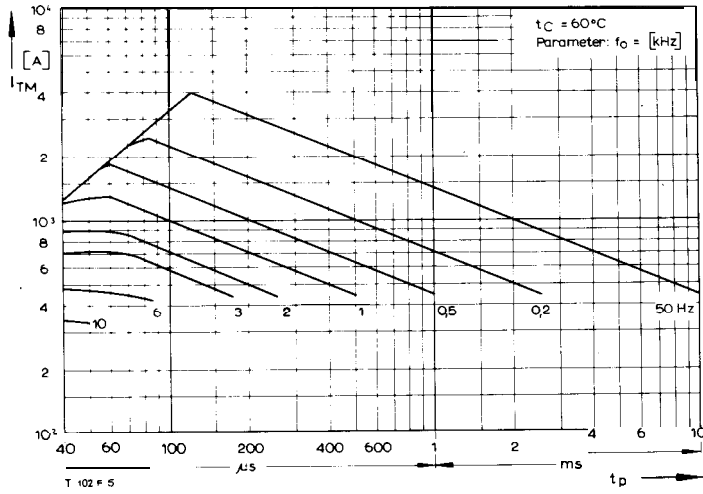
Mechanical properties

Si-Element mit Druckkontakt	Si-pellet with pressure contact		M	20 Nm
Anzugsdrehmoment	tightening torque		G	typ. 150g
Gewicht	weight			8mm
Kriechstrecke	Creepage distance			C
Feuchteklasse	humidity classification	DIN 40040		50 m/s ²
Schwingfestigkeit	Vibration resistance	f = 50 Hz		Seitelpage 154
Maßbild B	outline B	DIN 41892-20483		

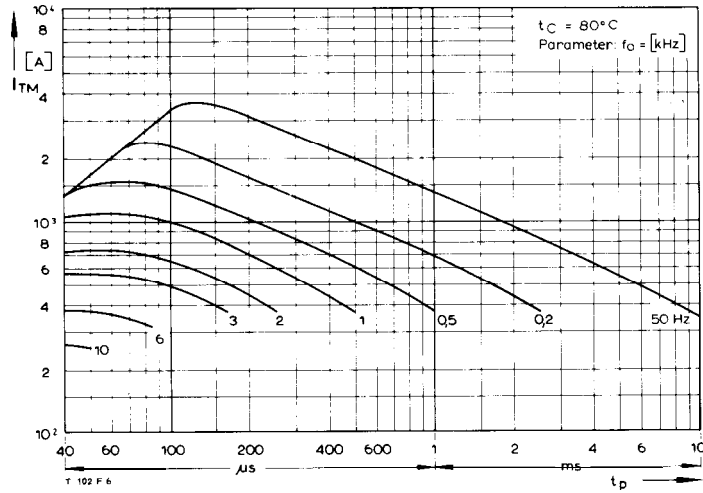
* Für größere Stückzahlen bitte Liefertermin erfragen/Delivery for larger quantities on request

1) Werte nach DIN IEC 747-6 (ohne vorausgehende Kommutierung)/Values to DIN IEC 747-6 (without prior commutation)

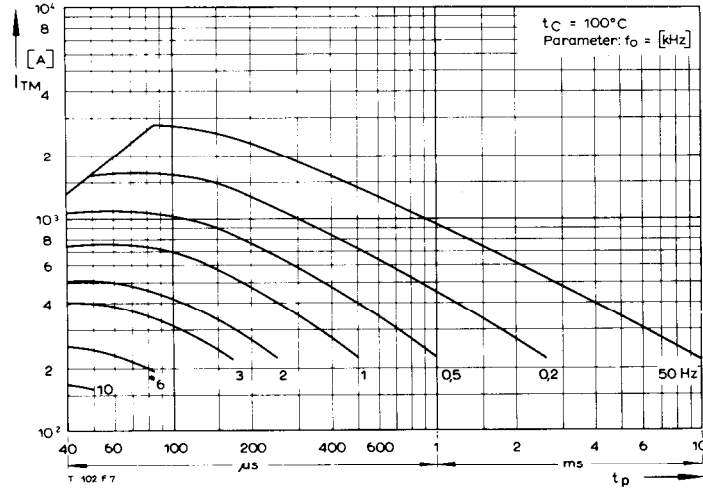
2) Unmittelbar nach der Freiwerdezeit, vgl. Meßbedingungen für t_i /Immediately after circuit commutated turn-off time, see Parameters t_i



Bild/Fig. 1



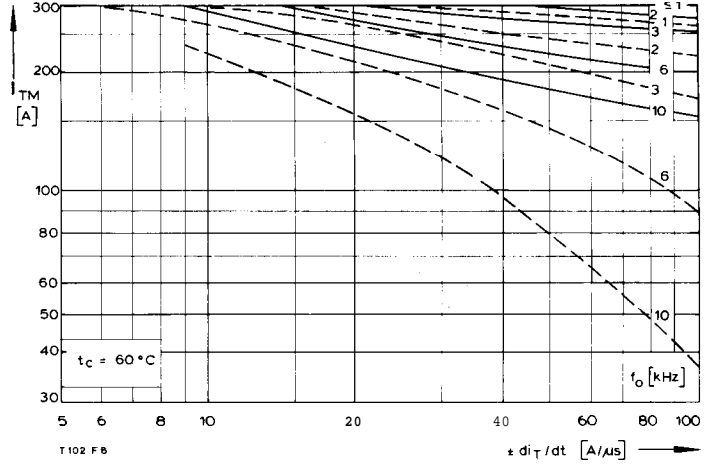
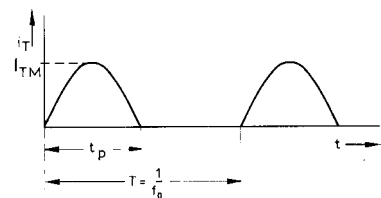
Bild/Fig. 2



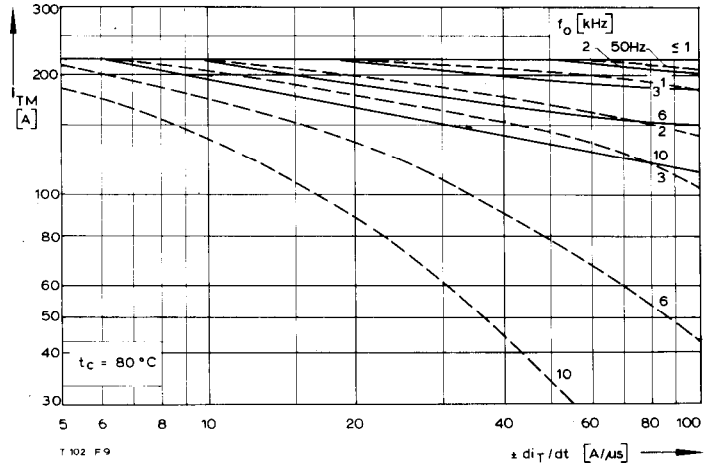
Bild/Fig. 3

Bild/Fig. 1, 2, 3
 Steuergenerator/pulse generator:
 $i_G = 0,6 \text{ A}$, $di_G/dt = 0,6 \text{ A}/\mu\text{s}$

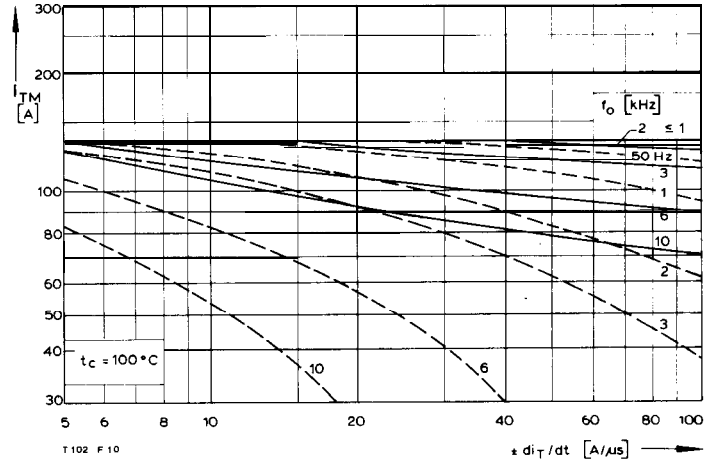
RC-Glied/RC-network:
 $R[\Omega] \geq 0,02 V_{DM} [V]$
 $C \leq 0,15 \mu\text{F}$
 $V_{DM} \leq 0,67 V_{DRM}$



Bild/Fig. 4



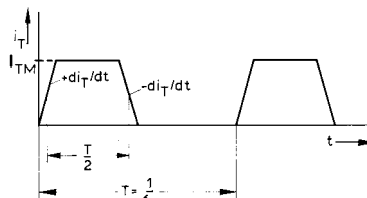
Bild/Fig. 5

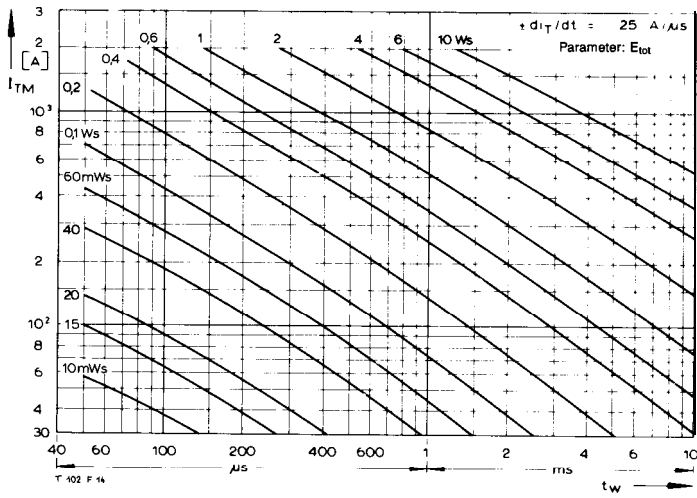


Bild/Fig. 6

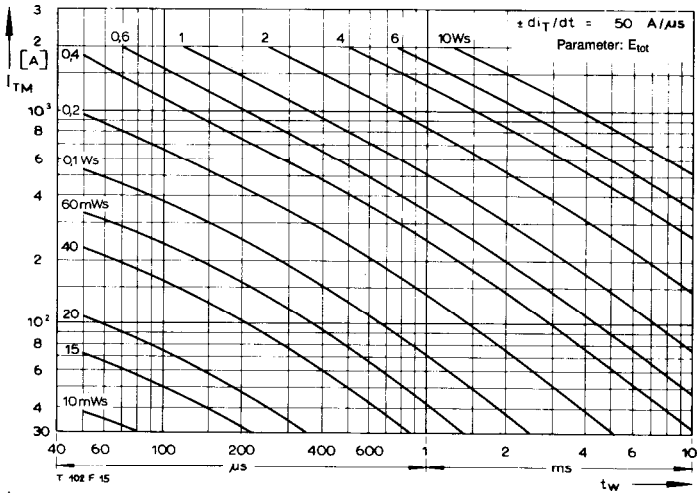
Bild/Fig. 4, 5, 6
 Steuergenerator/pulse generator:
 $i_G = 0,6 \text{ A}$, $di_G/dt = 0,6 \text{ A}/\mu\text{s}$

RC-Glied/RC-network:
 $R[\Omega] \geq 0,02 V_{DM} [V]$
 $C \leq 0,22 \mu\text{F}$
 $V_{DM} \leq 0,67 V_{DRM}$
 $dV_H/dt \leq 500 \text{ V}/\mu\text{s}$
 $V_{RM} \leq 0,67 V_{RRM}$

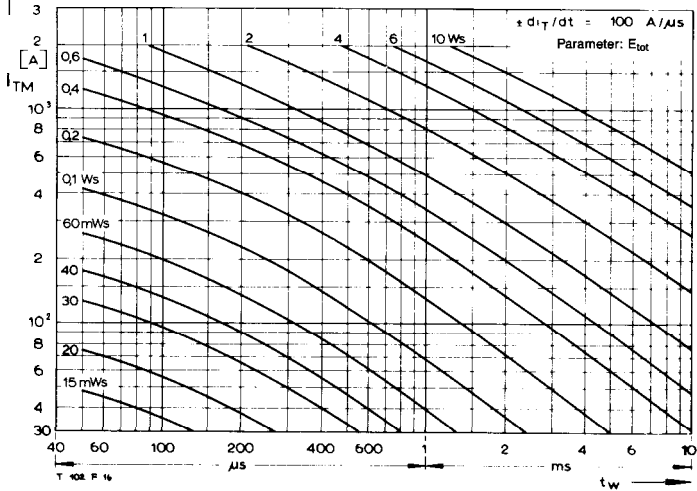




BildFig. 10



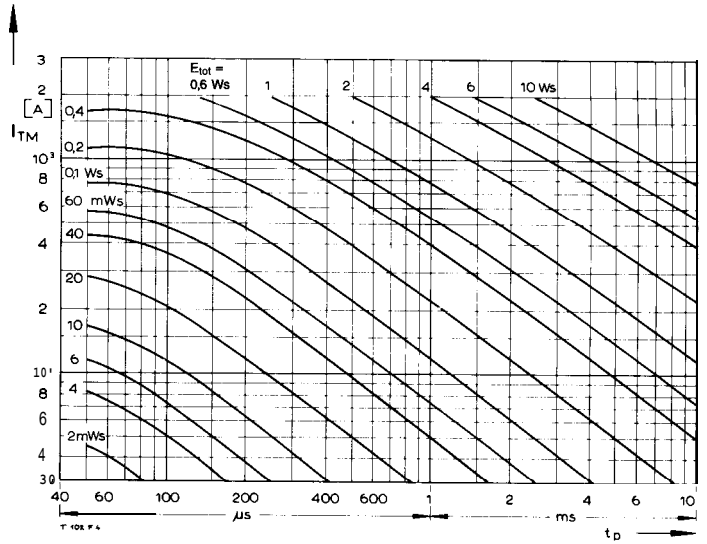
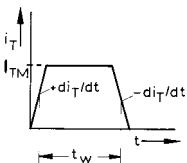
BildFig. 11



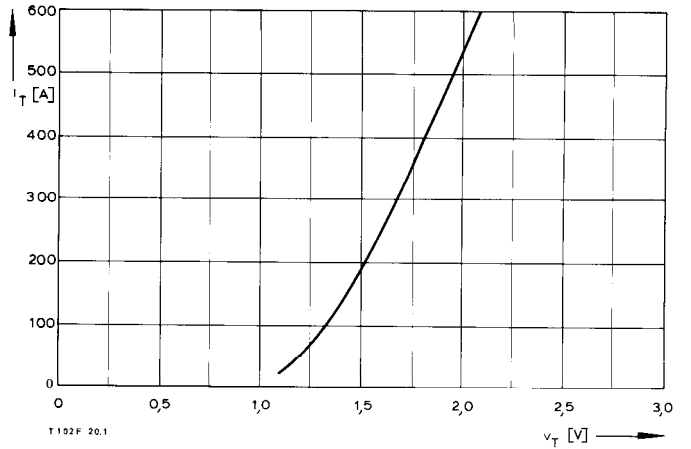
BildFig. 12

BildFig. 10, 11, 12
Steuergenerator/pulse generator:
 $i_G = 0,6 \text{ A}$, $di_G/dt = 0,6 \text{ A}/\mu\text{s}$

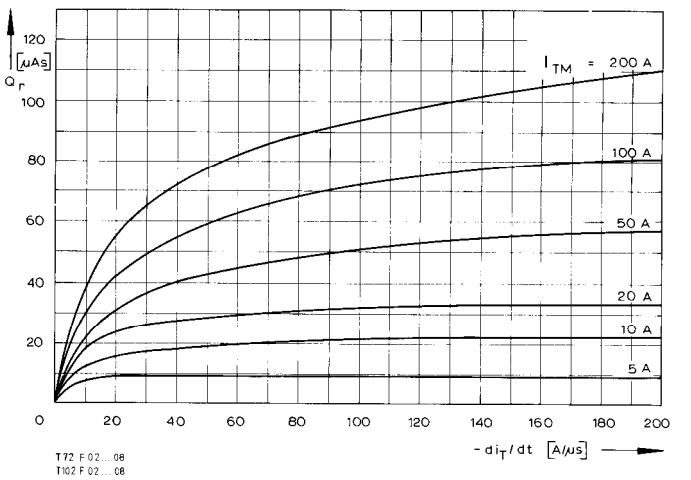
RC-Glied/RC-network:
 $R [\Omega] \geq 0,02 v_{DM} [\text{V}]$
 $C \leq 0,22 \mu\text{F}$
 $v_{DM} \leq 0,67 \text{ VD}_{\text{,}}$
 $dv_P/dt \leq 500 \text{ V}/\mu\text{s}$
 $v_{RM} \leq 0,67 V_{RRM}$



BildFig. 13



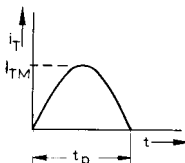
BildFig. 14

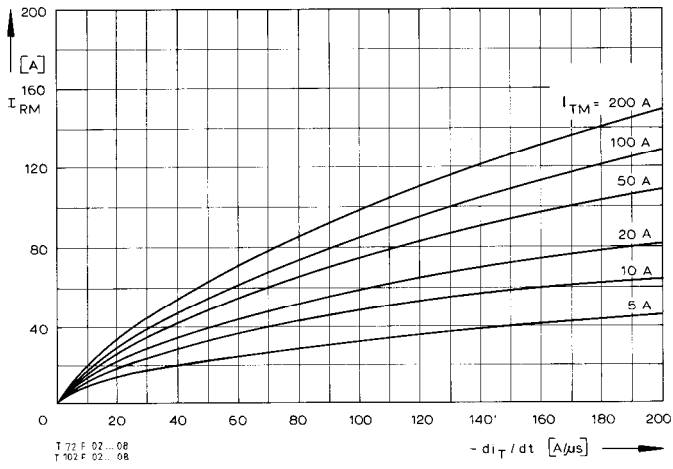


BildFig. 15

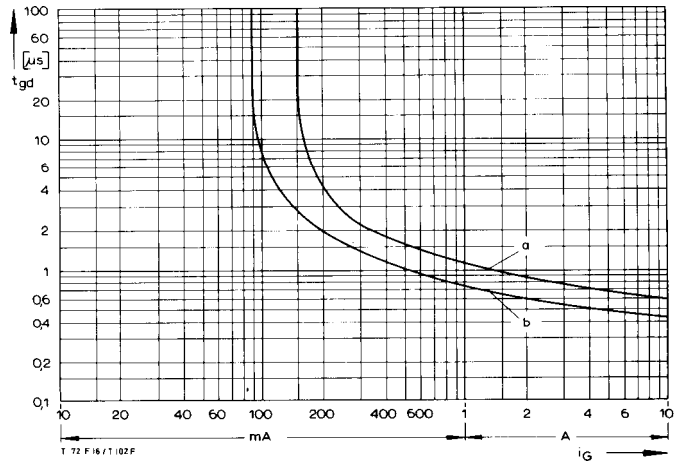
(zu Bild/ to Fig. 13)
Steuergenerator/pulse generator:
 $i_G = 0,6 \text{ A}$, $di_G/dt = 0,6 \text{ A}/\mu\text{s}$

RC-Glied/RC-network:
 $R [\Omega] \geq 0,02 v_{DM} [\text{V}]$
 $C \leq 0,15 \mu\text{F}$

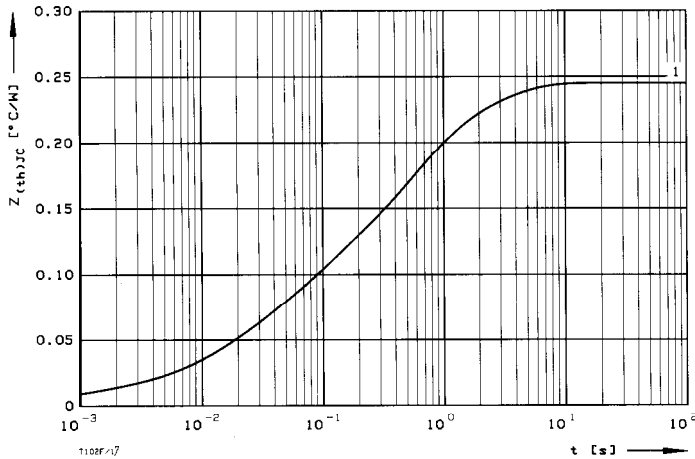




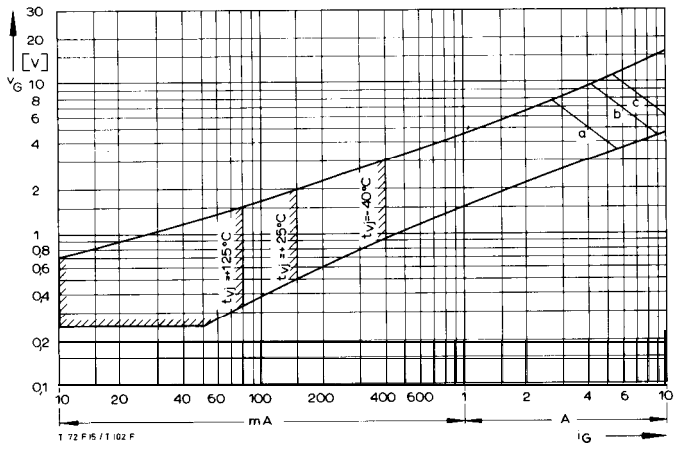
Bild/fig. 16
 Rückstromspitze $I_{RM} = f(-di/dt)$, $t_{vj} = t_{vj(max)}$, $V_R = 0.5 V_{RRM}$, $V_{RM} = 0.8 V_{RRM}$
 Peak reverse recovery current $I_{RM} = f(-di/dt)$, $t_{vj} = t_{vj(max)}$, $V_R = 0.5 V_{RRM}$, $V_{RM} = 0.8 V_{RRM}$
 Parameter: Durchlaßstrom/On-state current I_{TM}



Bild/fig. 18
 ZündverzugsGate controlled delay time $t_{gd} = f(I_{GM})$, $t_{vj} = 25^\circ\text{C}$, $di_G/dt = i_{GM}/1 \mu\text{s}$
 a – Maximaler Verlauf/Limiting Characteristic
 b – Typischer Verlauf/Typical Characteristic



Bild/fig. 17
 Transienter innerer Wärmewiderstand $Z_{tthJC} = f(t)$, DC
 Transient thermal impedance $Z_{tthJC} = f(t)$, DC



Bild/fig. 19
 Steuercharakteristik mit Zündbereichen/Gate Characteristic with triggering areas
 $V_G = f(I_G)$, $V_D = 6$ V

Parameter:	a	b	c
Steuerimpulsdauer/Trigger pulse duration t_g [ms]	10	1	0.5
Höchstzulässige Spitzensteuerverlustleistung/ Max. rated peak gate power dissipation P_{GM} [W]	20	40	60

Analytische Elemente des transienten Wärmewiderstandes Z_{tthJC} für DC
 Analytical elements of transient thermal impedance Z_{tthJC} for DC

POS. n	1	2	3	4	5	6	7
R_{thn} [$^\circ\text{C}/\text{W}$]	0,0081	0,033	0,054	0,1	0,05		
τ_n [s]	0,00081	0,014	0,066	0,5	2,3		

Analytische Funktion/analytical function:

$$Z_{tthJC} = \sum_{n=1}^{n_{max}} R_{thn} (1 - \text{EXP}(-t/\tau_n))$$